

Pavel A Yunin

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

117
papers

495
citations

12
h-index

15
g-index

118
ext. papers

567
ext. citations

1.3
avg, IF

3.53
L-index

#	Paper	IF	Citations
117	Small-molecule heterojunctions: Stability to ageing under sunlight. <i>Applied Surface Science</i> , 2022 , 578, 152084	6.7	1
116	Ion-Beam Synthesis of Gallium Oxide Nanocrystals in a SiO ₂ /Si Dielectric Matrix. <i>Nanomaterials</i> , 2022 , 12, 1840	5.4	0
115	Near-infrared stimulated emission from indium-rich InGaN layers grown by plasma-assisted MBE. <i>Applied Physics Letters</i> , 2021 , 118, 151902	3.4	1
114	Nanostructuring of Mn(II)Pc thin films by vacuum deposition in a weak magnetic field. <i>Vacuum</i> , 2021 , 194, 110584	3.7	1
113	Effect of the AlGaAs Seed Layer Composition on Antiphase Domains Formation in (Al)GaAs Structures Grown by Vapor-Phase Epitaxy on Ge/Si(100) Substrates. <i>Technical Physics Letters</i> , 2021 , 47, 413-416	0.7	1
112	Effect of the Chloropentafluoroethane Additive in Chlorine-Containing Plasma on the Etching Rate and Etching-Profile Characteristics of Gallium Arsenide. <i>Semiconductors</i> , 2021 , 55, 865-868	0.7	
111	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. <i>Journal of Applied Physics</i> , 2020 , 127, 165701	2.5	0
110	Synchrotron, X-Ray, and Electron Microscopic Studies of Catalyst Systems Based on Multiwalled Carbon Nanotubes Modified by Copper Nanoparticles. <i>Physics of the Solid State</i> , 2020 , 62, 214-222	0.8	4
109	SIMS Analysis of Carbon-Containing Materials: Content of Carbon Atoms in sp ² and sp ³ Hybridization States. <i>Technical Physics Letters</i> , 2020 , 46, 290-294	0.7	3
108	Possibilities of the Master Mask Method in Analysis of Characteristics of Planar HTSC Structures Depending on Superconducting Film Thickness. <i>Technical Physics</i> , 2020 , 65, 1605-1608	0.5	1
107	The Microstructure of Transition Boundaries in Multilayer Mo/Be Systems. <i>Technical Physics</i> , 2020 , 65, 1800-1808	0.5	0
106	Low-barrier Mott diodes with near-surface polarization-induced δ doping. <i>Applied Physics Letters</i> , 2020 , 116, 013505	3.4	1
105	Experimental Observation of s-Component of Superconducting Pairing in Thin Disordered HTSC Films Based on YBCO. <i>Physics of the Solid State</i> , 2020 , 62, 1598-1603	0.8	
104	Matched characterization of super-multiperiod superlattices. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 455103	3	4
103	Atomic Force Microscopy Examination of Elementary Processes in Metalorganic Compound Hydride Epitaxy of GaAs-Based Nanoheterostructures. <i>Technical Physics</i> , 2020 , 65, 791-794	0.5	
102	The Magnetoelectric Effect in Ferroelectric/Ferromagnetic Film Hybrid Systems with Easy-Plane and Easy-Axis Anisotropy. <i>Technical Physics</i> , 2020 , 65, 1832-1836	0.5	
101	Modification of the Ratio between sp ² - to sp ³ -Hybridized Carbon Components in PECVD Diamond-Like Films. <i>Semiconductors</i> , 2020 , 54, 1047-1050	0.7	

100	Formation of Ohmic Contacts to a Diamond-Like Carbon Layer Deposited on a Dielectric Diamond Substrate. <i>Semiconductors</i> , 2020 , 54, 1056-1058	0.7	
99	Carbon Films Produced by the Pulsed Laser Method and Their Influence on the Properties of GaAs Structures. <i>Semiconductors</i> , 2020 , 54, 1059-1063	0.7	2
98	Microwave Impedance of Thin-Film Superconductor/Normal Metal Hybrid Structures with a High Conductivity Ratio. <i>Physics of the Solid State</i> , 2019 , 61, 1675-1681	0.8	
97	Plasma-Chemical Deposition of Diamond-Like Films onto the Surface of Heavily Doped Single-Crystal Diamond. <i>Semiconductors</i> , 2019 , 53, 1203-1206	0.7	3
96	Phase Diagrams of Thin Disordered Films Based on HTSC YBa ₂ Cu ₃ O _{7-δ} in External Magnetic Fields. <i>Physics of the Solid State</i> , 2019 , 61, 1523-1528	0.8	3
95	Comparative Analysis of the Luminescence of Ge:Sb Layers Grown on Ge(001) and Si(001) Substrates. <i>Semiconductors</i> , 2019 , 53, 1318-1323	0.7	1
94	Misorientation Angle Dependence of Boron Incorporation Into CVD Diamond Delta Layers. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1800606	1.3	2
93	Microstructure and Density of Mo Films in Multilayer Mo/Si Mirrors. <i>Journal of Surface Investigation</i> , 2019 , 13, 8-13	0.5	
92	Emission Properties of Heavily Doped Epitaxial Indium-Nitride Layers. <i>Semiconductors</i> , 2019 , 53, 1357-1367	0.7	2
91	Influence of Thermal Annealing on the Properties of Multilayer Mo/Be Mirrors. <i>Technical Physics</i> , 2019 , 64, 1692-1697	0.5	2
90	Pulsed Ion-Beam Treatment of Germanium Implanted by Antimony Ions. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2019 , 55, 423-430	0.6	1
89	Magnetostriction Effect in Ferromagnetic Films with Easy-Axis and Easy-Plane Anisotropies. <i>Technical Physics</i> , 2019 , 64, 1646-1651	0.5	1
88	InN Layers Grown by MOCVD on a-Plane Al ₂ O ₃ . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700919	1.6	5
87	Synthesis of Hybrid Materials Based on Iron Nanoparticle-Decorated Multiwalled Carbon Nanotubes. <i>Inorganic Materials</i> , 2018 , 54, 233-236	0.9	1
86	Towards the indium nitride laser: obtaining infrared stimulated emission from planar monocrystalline InN structures. <i>Scientific Reports</i> , 2018 , 8, 9454	4.9	15
85	Influence of the Rotation Frequency of a Disk Substrate Holder on the Crystal Structure Characteristics of MOCVD-Grown GaAs Layers. <i>Technical Physics</i> , 2018 , 63, 211-215	0.5	1
84	MOCVD Growth of InGaAs/GaAs/AlGaAs Laser Structures with Quantum Wells on Ge/Si Substrates. <i>Crystals</i> , 2018 , 8, 311	2.3	9
83	Grazing Incidence X-Ray Diffraction Study of Tantalum Thin Films. <i>Journal of Surface Investigation</i> , 2018 , 12, 701-704	0.5	1

82	New Hybrid Material Based on Multiwalled Carbon Nanotubes Decorated by Rhenium-Tungsten Nanodendrites. <i>Journal of Surface Investigation</i> , 2018 , 12, 682-687	0.5	1
81	The Gas-Phase Synthesis of a New Functional Hybrid Material on the Basis of Multiwalled Carbon Nanotubes Decorated with Faceted Aluminum Nanocrystals. <i>Technical Physics Letters</i> , 2018 , 44, 865-868 ^{0.7}	0.7	6
80	A Study of the Isolation Region of Planar Superconducting YBCO Structures Formed by the Master Mask Method. <i>Physics of the Solid State</i> , 2018 , 60, 2139-2144	0.8	3
79	Verification of the Hypothesis on the Thermoelastic Nature of Deformation of a (0001)GaN Layer Grown on the Sapphire a-Cut. <i>Semiconductors</i> , 2018 , 52, 1491-1494	0.7	
78	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. <i>Semiconductors</i> , 2018 , 52, 1547-1550	0.7	3
77	Influence of thermal annealing on the electrical and luminescent properties of heavily Sb-doped Ge/Si(001) layers. <i>Semiconductor Science and Technology</i> , 2018 , 33, 124019	1.8	6
76	Investigation of the Anisotropy of the Structural Properties of GaN(0001) Layers Grown by MOVPE on a-Plane (11 $\bar{2}$ 0) Sapphire. <i>Semiconductors</i> , 2018 , 52, 1412-1415	0.7	1
75	Plasma Chemical Etching of Gallium Arsenide in C2F5Cl-Based Inductively Coupled Plasma. <i>Semiconductors</i> , 2018 , 52, 1473-1476	0.7	1
74	A New Limitation of the Depth Resolution in TOF-SIMS Elemental Profiling: the Influence of a Probing Ion Beam. <i>Technical Physics Letters</i> , 2018 , 44, 320-323	0.7	1
73	A Comparative Analysis of Catalysts for the Preparation of Germanium through Hydrogen Reduction of Germanium Tetrachloride. <i>Inorganic Materials</i> , 2018 , 54, 971-976	0.9	1
72	Study of the Structural and Morphological Properties of HPHT Diamond Substrates. <i>Semiconductors</i> , 2018 , 52, 1432-1436	0.7	4
71	New Cluster Secondary Ions for Quantitative Analysis of the Concentration of Boron Atoms in Diamond by Time-of-Flight Secondary-Ion Mass Spectrometry. <i>Technical Physics Letters</i> , 2018 , 44, 297-300 ^{0.7}	0.7	1
70	GaAs/Ge/Si epitaxial substrates: Development and characteristics. <i>AIP Advances</i> , 2017 , 7, 015304	1.5	17
69	YBa2Cu3O7 δ long Josephson junctions on bicrystal Zr1-xYxO2 substrates fabricated by preliminary topology masks. <i>Superconductor Science and Technology</i> , 2017 , 30, 025007	3.1	12
68	Specific features of the photoexcitation spectra of epitaxial InN layers grown by molecular-beam epitaxy with the plasma activation of nitrogen. <i>Semiconductors</i> , 2017 , 51, 1537-1541	0.7	
67	Peculiarities of growing InGaAs/GaAs/AlGaAs laser structures by MOCVD on Ge/Si substrates. <i>Semiconductors</i> , 2017 , 51, 1527-1530	0.7	5
66	Investigation of X-ray diffraction limitations upon the analysis of tellurium-atom injection into GaAs epitaxial layers. <i>Journal of Surface Investigation</i> , 2017 , 11, 361-365	0.5	1
65	Selective analysis of the elemental composition of InGaAs/GaAs nanoclusters by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , 2017 , 43, 477-480	0.7	0

64	Low-temperature deposition of SiN _x Films in SiH ₄ /Ar + N ₂ inductively coupled plasma under high silane dilution with argon. <i>Semiconductors</i> , 2017 , 51, 1449-1452	0.7	0
63	Epitaxial GaN layers formed on langasite substrates by the plasma-assisted MBE method. <i>Semiconductors</i> , 2016 , 50, 1511-1514	0.7	0
62	Phase transitions in hybrid SFS structures with thin superconducting layers. <i>JETP Letters</i> , 2016 , 104, 329-333		9
61	Heavily doped GaAs:Te layers grown by MOVPE using diisopropyl telluride as a source. <i>Semiconductors</i> , 2016 , 50, 1439-1442	0.7	2
60	A study of planar structures formed on the modified Al ₂ O ₃ surfaces determining the topology of superconducting elements during YBa ₂ Cu ₃ O _{7-δ} deposition. <i>Technical Physics Letters</i> , 2016 , 42, 594-597	0.7	8
59	Extremely deep profiling analysis of the atomic composition of thick (>100 nm) GaAs layers within power PIN diodes by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , 2016 , 42, 783-787	0.7	
58	High-coercivity magnetic mirror polarizers for thermal neutrons. <i>Journal of Surface Investigation</i> , 2016 , 10, 486-489	0.5	1
57	Pyrolytic deposition of nanostructured titanium carbide coatings on the surface of multiwalled carbon nanotubes. <i>Technical Physics Letters</i> , 2016 , 42, 517-519	0.7	8
56	Stimulated emission from a metamorphic GaAsSb bulk layer on a GaAs substrate. <i>Semiconductors</i> , 2016 , 50, 586-589	0.7	
55	Grazing incidence mirrors with enhanced reflectance in the soft X-ray region. <i>Thin Solid Films</i> , 2016 , 598, 156-160	2.2	6
54	Hydrogen reduction of 98MoF ₆ in RF discharge. <i>Journal of Radioanalytical and Nuclear Chemistry</i> , 2016 , 309, 833	1.5	5
53	Features of spectral properties of Sm(3+) complexes with dithia- and diselenophosphinate ligands. <i>Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy</i> , 2016 , 163, 134-9	4.4	12
52	On the use of an external reference sample in the X-ray diffraction analysis of epitaxial layers. <i>Journal of Surface Investigation</i> , 2016 , 10, 96-100	0.5	3
51	Characterization of interfaces in mosaic CVD diamond crystal. <i>Journal of Crystal Growth</i> , 2016 , 442, 62-67.6		14
50	Copper(II)berium(III) 15-metallacrown-5 based on glycinehydroxamic acid as a new precursor for heterobimetallic composite materials on carbon nanotubes. <i>Polyhedron</i> , 2016 , 114, 96-100	2.7	15
49	Terahertz radiation from bismuth surface induced by femtosecond laser pulses. <i>Optics Letters</i> , 2016 , 41, 4289-92	3	7
48	Monolithically integrated InGaAs/GaAs/AlGaAs quantum well laser grown by MOCVD on exact Ge/Si(001) substrate. <i>Applied Physics Letters</i> , 2016 , 109, 061111	3.4	19
47	Formation of singular (001) terraces on the surface of single-crystal HPHT diamond substrates. <i>Semiconductors</i> , 2016 , 50, 1622-1625	0.7	3

46	Influence of surface roughness on a change in the growth mode from two-dimensional to three-dimensional for strained SiGe heterostructures. <i>Semiconductors</i> , 2016 , 50, 1630-1634	0.7	1
45	Modification of YBa ₂ Cu ₃ O _{7-δ} thin films by ion implantation. <i>Journal of Surface Investigation</i> , 2016 , 10, 438-440	0.5	2
44	Nonlinear calibration curves in secondary ion mass spectrometry for quantitative analysis of GeSi heterostructures with nanoclusters. <i>Technical Physics Letters</i> , 2016 , 42, 243-247	0.7	2
43	Features of InN growth by nitrogen-plasma-assisted MBE at different ratios of fluxes of group-III and -V elements. <i>Semiconductors</i> , 2016 , 50, 261-265	0.7	4
42	Quantitative depth profiling of Si _{1-x} Gex structures by time-of-flight secondary ion mass spectrometry and secondary neutral mass spectrometry. <i>Thin Solid Films</i> , 2016 , 607, 25-31	2.2	5
41	Structural and optical properties of GaAsSb QW heterostructures grown by laser deposition. <i>Semiconductors</i> , 2015 , 49, 109-112	0.7	1
40	Plastic relaxation in GeSi layers on Si (001) and Si (115) substrates. <i>Semiconductors</i> , 2015 , 49, 19-22	0.7	
39	Thin single-crystal Ge layers on Si substrates. <i>Technical Physics Letters</i> , 2015 , 41, 36-39	0.7	6
38	Synthesis and properties of chitosan-poly lactide compositions produced with the use of compatibilizers. <i>Polymer Science - Series B</i> , 2015 , 57, 239-243	0.8	4
37	Electrical conductivity of vacuum deposited films and crystals of redox-isomeric semiquinonato cobalt complexes. <i>Solid State Sciences</i> , 2015 , 48, 13-18	3.4	4
36	Graft and block copolymers of chitosan with vinyl monomers: Synthesis, structure, and properties. <i>Polymer Science - Series B</i> , 2015 , 57, 93-105	0.8	12
35	Raman spectroscopy of InGaAs/GaAs nanoheterostructures doped with Mn. <i>Semiconductors</i> , 2015 , 49, 99-103	0.7	2
34	High-rate growth of InN films on sapphire and sapphire substrates by metalorganic vapor phase epitaxy with plasma-assisted nitrogen activation. <i>Technical Physics Letters</i> , 2015 , 41, 266-269	0.7	1
33	Kinetics and formation mechanism of yttrium aluminum garnet from an amorphous phase prepared by the sol-gel method. <i>Ceramics International</i> , 2015 , 41, 10616-10623	5.1	10
32	New hybrid material based on multiwalled carbon nanotubes decorated with rhenium nanoparticles. <i>Journal of Surface Investigation</i> , 2015 , 9, 694-698	0.5	8
31	Impact of growth and annealing conditions on the parameters of Ge/Si(001) relaxed layers grown by molecular beam epitaxy. <i>Semiconductors</i> , 2015 , 49, 1415-1420	0.7	18
30	The waveguide effect of InGaAs quantum wells in a GaAs structure on Si substrate with Ge buffer layer. <i>Technical Physics Letters</i> , 2015 , 41, 648-650	0.7	2
29	Single-crystal GaN/AlN layers on CVD diamond. <i>Technical Physics Letters</i> , 2015 , 41, 954-956	0.7	

28	Growth of light-emitting SiGe heterostructures on strained silicon-on-insulator substrates with a thin oxide layer. <i>Semiconductors</i> , 2015 , 49, 1104-1110	0.7	3
27	Continuous monitoring of temperature and rate of plasma etching of semiconductor wafers. <i>Applied Physics Letters</i> , 2015 , 107, 111601	3.4	3
26	Homoepitaxial growth of CVD diamond after ICP pretreatment. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 2572-2577	1.6	25
25	A new approach to express ToF SIMS depth profiling. <i>Surface and Interface Analysis</i> , 2015 , 47, 771-776	1.5	11
24	Terahertz-range spontaneous emission under the optical excitation of donors in uniaxially stressed bulk silicon and SiGe/Si heterostructures. <i>Semiconductors</i> , 2015 , 49, 13-18	0.7	
23	Application of a pseudomorphous layer on a vicinal substrate as a test sample for high-resolution X-ray diffractometry. <i>Journal of Surface Investigation</i> , 2015 , 9, 1243-1250	0.5	2
22	Peculiarities in magnetron sputtering of YBCO epitaxial films for applications in superconductor electronics devices. <i>Technical Physics</i> , 2015 , 60, 1682-1688	0.5	8
21	Si ₃ N ₄ layers for the in-situ passivation of GaN-based HEMT structures. <i>Semiconductors</i> , 2015 , 49, 1421-1424	0.7	6
20	The role of ultra-thin carbon barrier layers for fabrication of La/B ₄ C interferential mirrors: Study by time-of-flight secondary ion mass spectrometry and high-resolution transmission electron microscopy. <i>Thin Solid Films</i> , 2015 , 577, 11-16	2.2	13
19	Quantitative calibration and germanium SIMS depth profiling in Ge x Si _{1-x} /Si heterostructures. <i>Semiconductors</i> , 2014 , 48, 1109-1117	0.7	5
18	A new approach to the diagnostics of nanoislands in Ge x Si _{1-x} /Si heterostructures by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , 2014 , 40, 601-605	0.7	7
17	Use of related parameters in X-ray diffraction analysis of multilayer structures with allowance for the layer growth time. <i>Technical Physics</i> , 2014 , 59, 402-406	0.5	3
16	Raman spectra of amorphous isotope-enriched ⁷⁴ Ge with low-strained Ge nanocrystals. <i>Thin Solid Films</i> , 2014 , 552, 46-49	2.2	4
15	Recovery of SIMS depth profiles with account for nonstationary effects. <i>Applied Surface Science</i> , 2014 , 307, 33-41	6.7	13
14	Growth and formation of the microstructure of YBCO films deposited by magnetron sputtering on sapphire substrates. <i>Technical Physics</i> , 2014 , 59, 1487-1491	0.5	3
13	Coulomb centers assisted tunneling in a doped triple barrier SiGe heterostructure. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2014 , 57, 42-46	3	
12	A new alternative to secondary Cs ⁺ ions for depth profiling of multilayer metal structures by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , 2013 , 39, 46-50	0.7	3
11	Depth profiling of fullerene-containing structures by time-of-flight secondary ion mass spectrometry. <i>Technical Physics Letters</i> , 2013 , 39, 1097-1100	0.7	8

10	Study of multilayered SiGe semiconductor structures by X-ray diffractometry, grazing-incidence X-ray reflectometry, and secondary-ion mass spectrometry. <i>Semiconductors</i> , 2013 , 47, 1556-1561	0.7	4
9	Changes in the elemental composition and microstructure of an YBa ₂ Cu ₃ O ₇ target during magnetron sputtering. <i>Technical Physics Letters</i> , 2013 , 39, 862-865	0.7	1
8	Experimental shift allowance in the deconvolution of SIMS depth profiles. <i>Surface and Interface Analysis</i> , 2013 , 45, 1228-1232	1.5	13
7	Sputter depth profiling of Mo/B ₄ C/Si and Mo/Si multilayer nanostructures: A round-robin characterization by different techniques. <i>Thin Solid Films</i> , 2013 , 540, 96-105	2.2	21
6	Monocrystalline InN Films Grown at High Rate by Organometallic Vapor Phase Epitaxy with Nitrogen Plasma Activation Supported by Gyrotron Radiation. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 110201	1.4	3
5	New approach to the X-ray diffraction analysis of test structures during flow calibration in epitaxial growth reactors. <i>Journal of Surface Investigation</i> , 2012 , 6, 494-497	0.5	2
4	Layer-by-layer analysis of structures containing δ layers by secondary ion mass spectrometry taking into account the TOF.SIMS-5 depth resolution function. <i>Journal of Surface Investigation</i> , 2012 , 6, 574-577	0.5	2
3	Analysis of the composition of (Al,Ga)As alloys by secondary ion mass spectroscopy and X-ray diffractometry. <i>Semiconductors</i> , 2012 , 46, 1392-1395	0.7	2
2	Method for taking into account the shift parameter in the deconvolution of the depth composition distribution of semiconductor structures from SIMS depth profiles. <i>Semiconductors</i> , 2012 , 46, 1481-1486	0.7	5
1	Direct comparison of superlattice periods measured with X-ray diffractometry and optical interferometry. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2011 , 75, 40-43	0.4	2